

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/626,550	07/25/2003	Se-Yeul Bae	009844-0305239 9321 EXAMINER	
909 7	1590 01/13/2005			
PILLSBURY WINTHROP, LLP			MALSAWMA, LALRINFAMKIM HMAR	
P.O. BOX 10500 MCLEAN, VA 22102			ART UNIT	PAPER NUMBER
			2825	
			DATE MAILED: 01/13/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/626,550	BAE, SE-YEUL				
Office Action Summary	Examiner	Art Unit				
	Lex Malsawma	2825				
- The MAILING DATE of this communication appears on the cover sheet with the correspondence address - Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status	•					
1) Responsive to communication(s) filed on 12 October 2004.						
2a)⊠ This action is FINAL . 2b)☐ This						
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
4) Claim(s) 1 and 5-8 is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>1 and 5-8</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or	election requirement.					
Application Papers						
9) The specification is objected to by the Examiner.						
10)⊠ The drawing(s) filed on <u>25 July 2003</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119	•	·				
12)⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a)⊠ All b)□ Some * c)□ None of:						
1. Certified copies of the priority documents have been received.						
2. Certified copies of the priority documents have been received in Application No						
3. Copies of the certified copies of the priority documents have been received in this National Stage						
application from the International Bureau (PCT Rule 17.2(a)).						
* See the attached detailed Office action for a list of the certified copies not received.						
Attachment(s)						
1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413)						
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SR/08) 5) Notice of Informal Patent Application (PTO-152)						
Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Solution (PTO-152) Notice of Informal Patent Application (PTO-152) Paper No(s)/Mail Date 6) Other:						

Application/Control Number: 10/626,550

Art Unit: 2825

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1 and 5-8 are rejected under 35 U.S.C. 102(b) as being anticipated by **Aoki** (6,387,821).

Regarding claims 1 and 5-8:

Aoki discloses (in Figs. 1-4 and Col. 8, lines 18-65) a method of forming metal wiring in a semiconductor device comprising:

forming a bottom metal pattern 105 on a semiconductor substrate (Col. 8, lines 4-5);

forming a low-temperature oxide (HSQ) an insulating layer 106 on the semiconductor substrate including the bottom metal pattern, wherein the low-temperature oxide (HSQ) is formed at the temperature of 400 °C (Col. 8, lines 26-28) and having a thickness of 1200 nm (12000 Å);

forming a first photoresist pattern 107 (Fig. 2a) for forming via hole on the low temperature oxide 106;

forming an unfinished via hole by removing the low temperature oxide selectively for a prescribed thickness using the first photoresist pattern as a mask (Fig. 2b), wherein the unfinished via hole is formed to make the thickness of the insulating layer 106 remaining inside the via hole equal to the thickness of the upper part of the damascene contact (i.e., the thickness

Application/Control Number: 10/626,550

Art Unit: 2825

of remaining insulating layer 106 below the unfinished via in Fig. 3a is equal to the thickness of the upper part of the damascene opening in Fig. 3b);

removing the first photoresist pattern 107 (Figs. 2a-2b);

forming a second photoresist pattern 108 for forming damascene pattern on the low temperature oxide around the unfinished via hole (Fig. 3a);

forming a damascene pattern by removing the low temperature oxide 106 selectively using the second photoresist pattern as a mask (Fig. 3b),;

removing the second photoresist pattern 108 (Figs. 3a-3b); and

forming a metal-wiring-via-damascene contact 111 by filling metal 111 (copper) in the damascene pattern, wherein the damascene contact is formed by dry deposition (i.e., sputtering) of metal on the insulating layer including the damascene pattern and the planarizing the metal 111 by CMP process (Figs. 4a-4b and Col. 8, lines 58-65).

Therefore, claims 1 and 5-8 are anticipated.

Remarks

3. Applicant's remarks/arguments have been carefully reviewed and considered, but they are not persuasive for the following reasons. Applicant's assert that Aoki does not disclose the use of a low temperature oxide as the insulating layer and that Aoki does not disclose forming the low temperature oxide at the temperature. However, Aoki discloses forming an HSQ film wherein Aoki shows (in Col. 5, lines 46-60) the chemical structure of HSQ, which is an oxide; and Aoki specifies (in Col. 8, lines 26-28), "heat treatment was conducted...at 400 °C for 60 minutes to form a HSQ film 106". Therefore, Applicant's assertion is not persuasive.

Application/Control Number: 10/626,550

Art Unit: 2825

Applicant's further assert that Aoki does not disclose a thickness of the low temperature oxide remaining inside the via hole is equal to a thickness of the upper part of the damascene contact. Contrary to Applicant's assertion, Aoki does indeed disclose (in Figs. 2b and 3b) this feature, i.e., note in Fig. 2b that the HSQ remaining inside/under the via is equal in thickness to the upper part of the damascene contact portion in Fig. 3b. Therefore, Applicant's further assertion is not persuasive; accordingly, all pending claims stand rejected under 35 USC § 102.

Conclusion

4. THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lex Malsawma whose telephone number is 571-272-1903. The examiner can normally be reached on Mon-Fri (8 hours between 5:30AM and 10:00 PM EST).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Lex Malsawma

January 10, 2005

MATTHEW SMITH
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800